

### FEATURES

- Circular Active Area
- Ideal for EUV Detection
- 100% Internal Quantum Efficiency
- High Speed
- Grid lines 5 microns, Pitch 100 microns
- Superior Radiation Hardness
- High Photon Flux Robustness
- TO-8 package
- Protective Cover Plate<sup>3</sup>

### Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	$\Phi 5.01$ mm		20		mm <sup>2</sup>
Responsivity	(see graph on next page)				A/W
Reverse Breakdown Voltage, $V_R$	$I_R = 1 \mu A$	160			Volts
Capacitance, C	$V_R = 0$ V		200	800	pF
Rise Time	$R_L = 50 \Omega, V_R = 150$ V			3.5	nsec
Dark Current	$V_R = 150$ V			100	nA

### Thermal Parameters

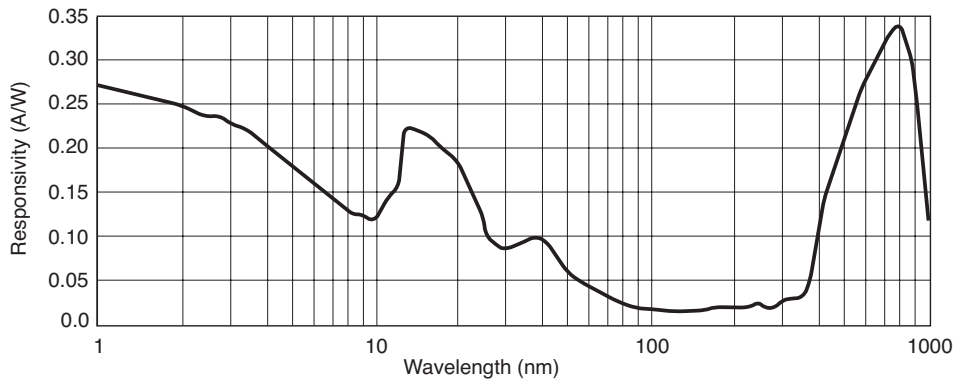
Storage and Operating Temperature Range	Units
Ambient <sup>1</sup>	-10 ° to 40 °C
Nitrogen or Vacuum	-20 °C to 80 °C
Lead Soldering Temperature <sup>2</sup>	260 °C

<sup>1</sup> Temperatures exceeding these parameters may create oxide growth on the active area.  
 Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

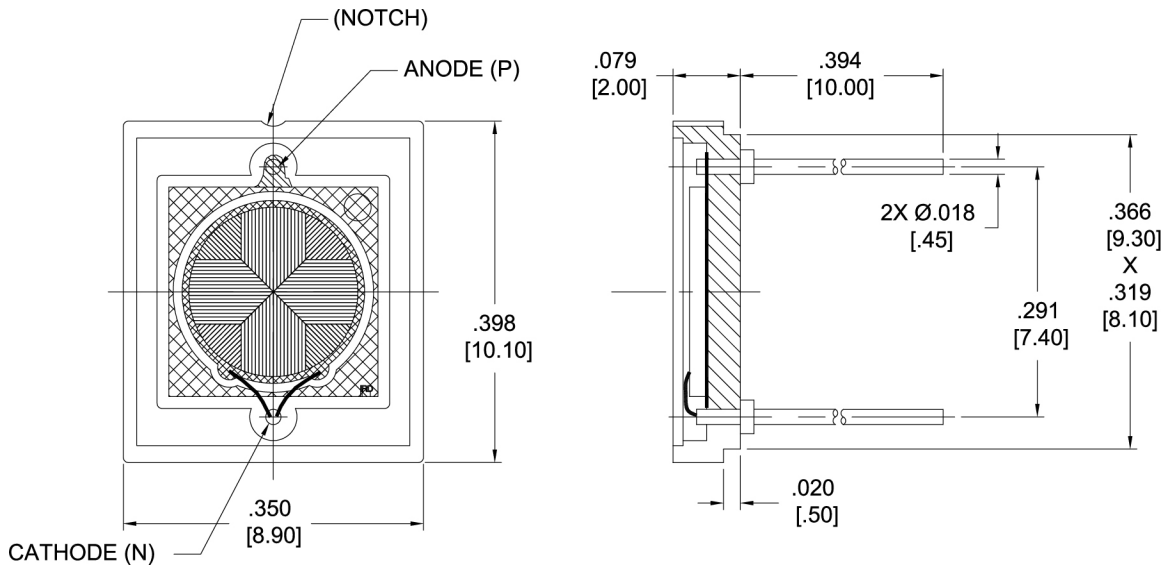
<sup>2</sup> 0.080" from case for 10 seconds.

<sup>3</sup> Shipped with temporary cover to protect the photodiode array and wire bonds.  
 Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

**Typical Photon Responsivity**



**Package Information**



Dimensions are in inch [metric] units.

**Ordering Information**

ODD-SXU-004      High Speed EUV Photodetector in TO8 Package Shipped with Protective Cover

Specifications are subject to change without prior notice.